

P-Channel 40 V (D-S) MOSFET

DESCRIPTION

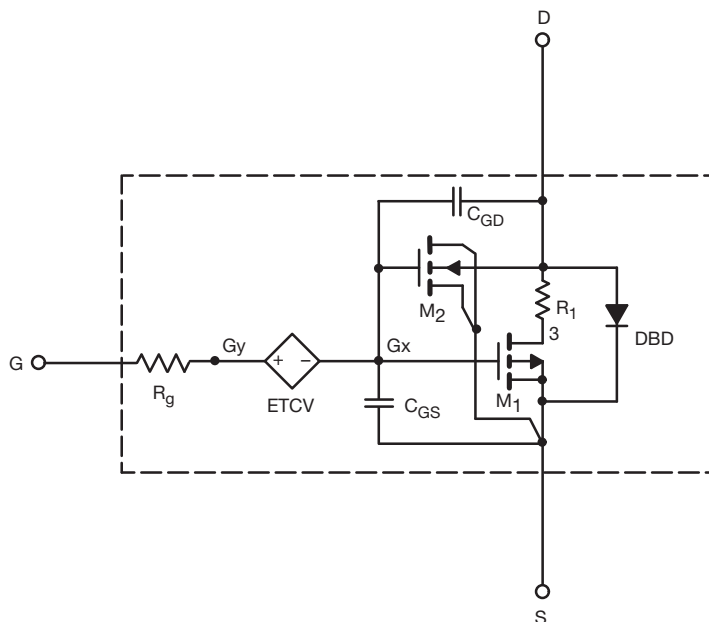
The attached SPICE model describes the typical electrical characteristics of the P-Channel vertical DMOS. The subcircuit model is extracted and optimized over the -55 °C to +150 °C temperature ranges under the pulsed -20 V to +20 V gate drive. The saturated output impedance is best fit at the gate bias near the threshold voltage.

A novel gate-to-drain feedback capacitance network is used to model the gate charge characteristics while avoiding convergence difficulties of the switched C_{gd} model. All model parameter values are optimized to provide a best fit to the measured electrical data and are not intended as an exact physical interpretation of the device.

CHARACTERISTICS

- P-channel vertical DMOS
- Macro model (subcircuit model)
- Level 3 MOS
- Apply for both linear and switching application
- Accurate over the -55 °C to +150 °C temperature range
- Model the gate charge

SUBCIRCUIT MODEL SCHEMATIC



Note

- This document is intended as a SPICE modeling guideline and does not constitute a commercial product datasheet. Designers should refer to the appropriate datasheet of the same number for guaranteed specification limits



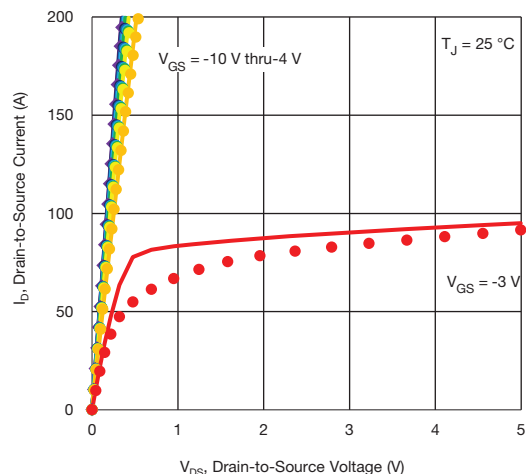
SPECIFICATIONS ($T_J = 25\text{ }^{\circ}\text{C}$, unless otherwise noted)					
PARAMETER	SYMBOL	TEST CONDITIONS	SIMULATED DATA	MEASURED DATA	UNIT
Static					
Gate-source threshold voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\text{ }\mu\text{A}$	-1.9	-	V
Drain-source on-state resistance ^a	$R_{DS(on)}$	$V_{GS} = -10\text{ V}$, $I_D = -20\text{ A}$	0.001725	0.0018	Ω
		$V_{GS} = -4.5\text{ V}$, $I_D = -20\text{ A}$	0.00225	0.0023	
Forward transconductance ^a	g_{fs}	$V_{DS} = -15\text{ V}$, $I_D = -20\text{ A}$	161	125	S
Body diode voltage	V_{SD}	$I_F = -10\text{ A}$, $V_{GS} = 0\text{ V}$	0.72	0.75	V
Dynamic ^b					
Input capacitance	C_{iss}	$V_{DS} = -15\text{ V}$, $V_{GS} = 0\text{ V}$, $f = 1\text{ MHz}$	21650	21850	pF
Output capacitance	C_{oss}		1658	1500	
Reverse transfer capacitance	C_{rss}		1448	1320	
Total gate charge	Q_g	$V_{DS} = -15\text{ V}$, $V_{GS} = -10\text{ V}$, $I_D = -20\text{ A}$	392	392	nC
			197	180	
Gate-source charge	Q_{gs}	$V_{DS} = -15\text{ V}$, $V_{GS} = -4.5\text{ V}$, $I_D = -20\text{ A}$	67	65	
Gate-drain charge	Q_{gd}		53	59	

Notes

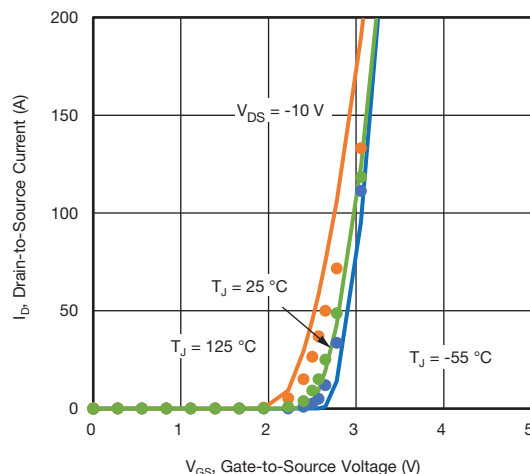
- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$
b. Guaranteed by design, not subject to production testing



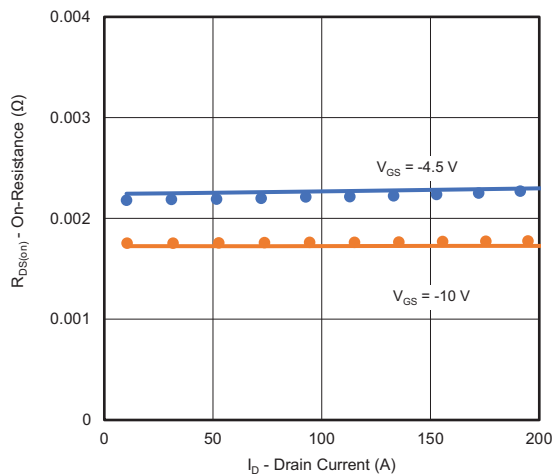
COMPARISON OF MODEL WITH MEASURED DATA ($T_J = 25^\circ\text{C}$, unless otherwise noted)



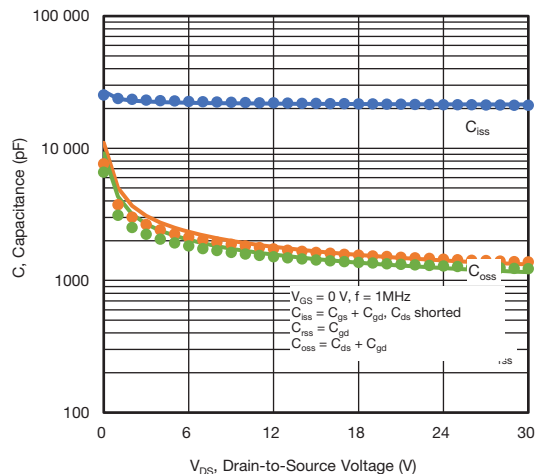
Output Characteristics



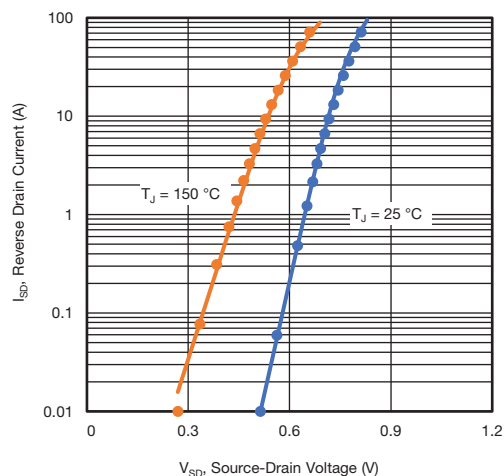
Transfer Characteristics



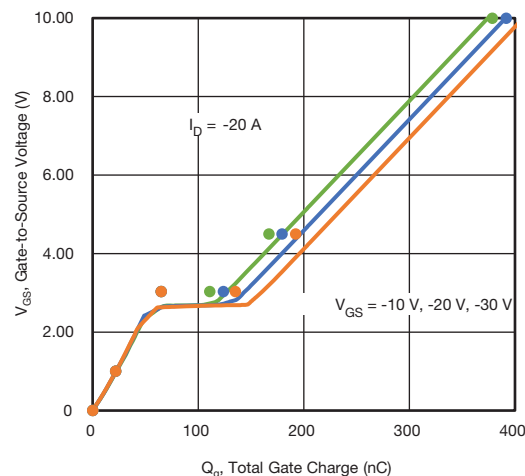
On-Resistance vs. Source Current and Gate Voltage



Capacitance



Source-Drain Diode Forward Voltage



Gate Charge